

Silicon NPN Power Transistors

2SC3152

DESCRIPTION

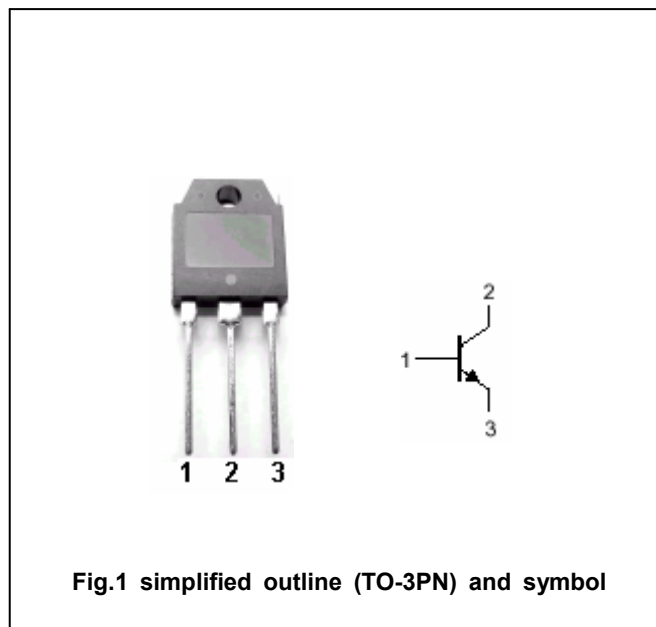
- With TO-3PN package
- High breakdown voltage ($V_{CBO} \geq 900V$)
- Fast switching speed
- Wide ASO □ Safe Operating Area □

APPLICATIONS

- 800V/3A Switching Regulator Applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	900	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		3	A
I_{CM}	Collector current-peak		10	A
I_B	Base current		1.5	A
P_C	Collector power dissipation	$T_C = 25^\circ\text{C}$	80	W
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55~150	°C

Silicon NPN Power Transistors

2SC3152

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=5mA ; R_{BE}=\infty$	800			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	900			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=1.5A ; I_B=0.3A$			2.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=1.5A ; I_B=0.3A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=800V ; I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			10	μA
h_{FE-1}	DC current gain	$I_C=0.2A ; V_{CE}=5V$	10		40	
h_{FE-2}	DC current gain	$I_C=1A ; V_{CE}=5V$	8			
C_{OB}	Output capacitance	$I_E=0 ; V_{CB}=10V ; f=1MHz$		60		pF
f_T	Transition frequency	$I_C=0.2A ; V_{CE}=10V$		15		MHz

Switching times

t_{on}	Turn-on time	$I_C=2A ; I_{B1}=0.4A ; I_{B2}=-0.8A$ $R_L=20\Omega, V_{CC}=400V$			1.0	μs
t_s	Storage time				3.0	μs
t_f	Fall time				0.7	μs

◆ h_{FE-1} classifications

K	L	M
10-20	15-30	20-40

Silicon NPN Power Transistors

2SC3152

PACKAGE OUTLINE

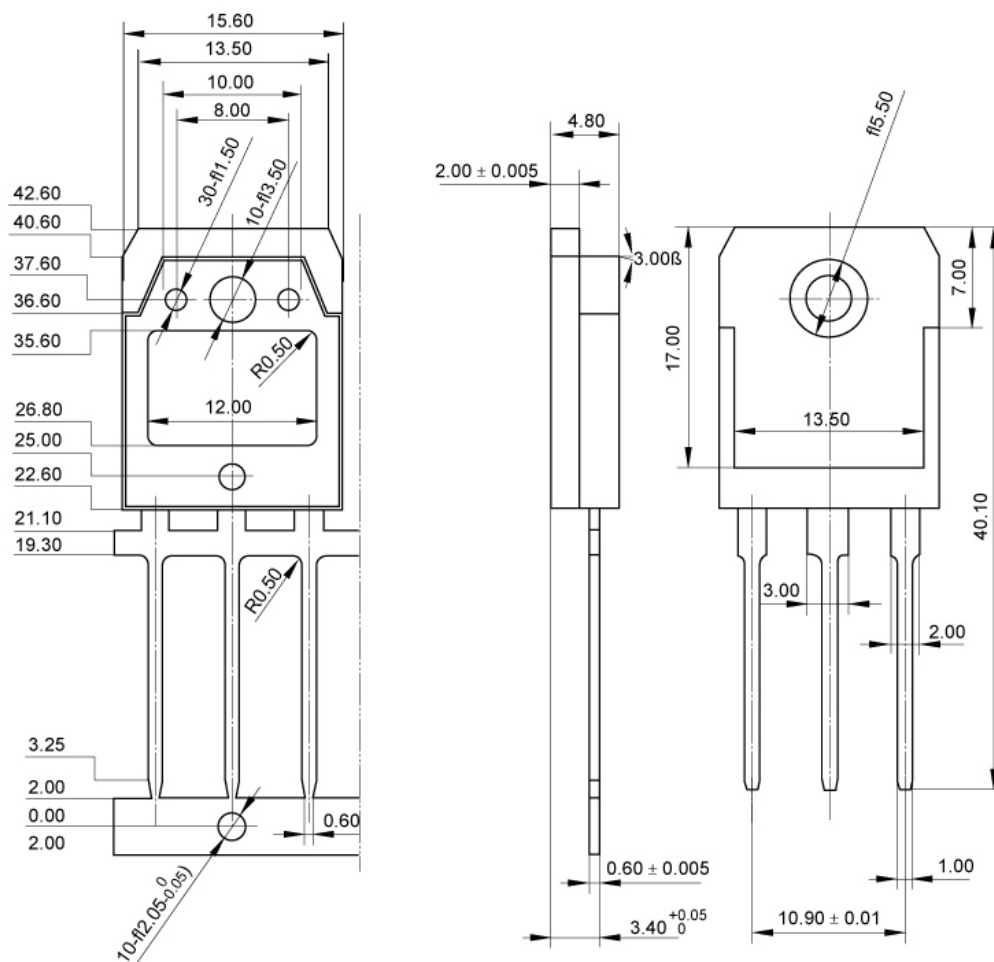


Fig.2 outline dimensions

Silicon NPN Power Transistors

2SC3152

